Electron transmission between normal and heavy electron metallic phases in Kondo lattices

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The interface between a heavy ferm ion m etallic phase and a \normal" (light-ferm ion) m etalphase is discussed. The Ferm im omentum m ism atch between the two phases causes the carriers to scatter at the interface. The interface conductance is a monotonous increasing function of conduction electron density, n_c , and is almost 60% of that of a clean heavy ferm ion m etal at half-lling ($n_c = 1$) and can be measured experimentally. Interface experiments can be used as probe of the nature of the homogenous heavy-ferm ion state and provide important information on the elects of inhomogeneities in heavy-ferm ion alloys.

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I. INTRODUCTION

In Kondo lattice metals a Fermisea of carriers interacts antiferrom agnetically with a lattice of localized f electrons, in rare earth atoms, which behave as localized m agnetic m om ents. The interplay between m agnetic interactions (such as RKKY) and the Kondo e ect leads to two very dierent types of ground states: a magnetically ordered m etaland a param agnetic disordered heavy m etalphase. On one hand, in the disordered phase the f m om ents e ectively decouple from the conduction band which has a small Ferm i sea (FS) made out of n_c electrons per unit cell. In the heavy-ferm ion liquid (HFL) phase, on the other hand, the K ondo e ect drives the form ation of singlets between conduction and f electrons and, therefore, leads to magnetic screening and a large FS with $n_c + 1$ electrons⁴. Hence, on a quantum phase transition (T = 0) between a heavy-ferm ion and a lightferm ion state the metal undergoes an abrupt change in the volume of the FS. This volume change can be observed in measurements of the Hall coe cient which is a direct measure of the density of carriers in the system 5 . Nevertheless, these measurements are often complicated by extrinsic e ects such as the presence of disorder and nite tem perature broadening.

In the presence of disorder, either due to alloying or extrinsic in purities, the situation becomes more complex and, due to local variations of them ical pressure, the system may break up into domains of the two phases leading to the formation of internal interfaces and to non-Fermi liquid behavior generated by quantum Grifths singularities⁶. A similar situation occurs close to a heavy-metal to Anderson insulator transition⁷. It has been argued recently^{8,9} that these interfaces control the amount of dissipation and the crossover energy scales

Now imagine that one constructs an interface (or junction) between these two distinct phases. The di erence in FS volume (or Ferm im om entum, $k_{\rm F}$, m ism atch) leads to an impedance at the interface and hence to a contribution to the conductance in the system (see Fig. 1). Similar experim ents have been realized recently in point contact spectroscopy of normal metals and heavy fermion superconductors such as CeCoIn₅, with unusual behavior of the point contact conductance as a function of the applied voltage¹⁰. We analyze below a inhomogeneous system in which a heavy ferm ion phase and a \norm al" (lightferm ion) metallic phase in the same material are in direct contact with each other. Because the K ondo singlet form ation lowers the energy of the conduction electrons, som e electrons m igrate from the norm alphase into the HFL phase, creating an electric dipole barrier between the two phases. At the interface the Ferm i surface volum e changes abruptly, so the interface itself behaves as a scatterer. We establish the matching conditions on the electronic states and calculate the electrical conductance across the interface in a simple K ondo lattice model.

We also provide suggestions for experiments where two phases are made to coexist in a single sample, as in Fig.1. The total resistance is given by the sum of the bulk resistances of the phases plus the interface contribution. If the specimen is a heavy ferm ion material belonging to the class of quantum critical points (QCPs) where the Kondo temperature vanishes, the interface scattering should be observable. If the material belongs to the \SDW scenario" of QCP, the interface contribution should be absent as there is no FS volume mismatch at the QCP. Therefore, such an experiment could distinguish the two types of QCPs.

The paper is organized as follows. The model H am iltonian is introduced in Section III; Section III is devoted to the discussion of the electronic properties of the interface; experimental suggestions are given in section IV.

that regulate the physical properties of disordered alloys. Therefore, our studies also have in plications on the study of non-Ferm i liquid phases 11 .

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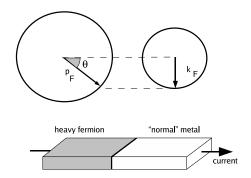


FIG. 1: Top: Ferm i surfaces of a heavy Ferm i liquid (HFL) metal (left) and a \normal" light ferm ion metal (right). Bottom: an experimental setup where the HFL and \normal" metal coexist in the same sample and an electrical current ows through.

II. M ODEL HAM ILTONIAN

W e consider a K ondo lattice m odel for the m etal, w ith a single band (k) of conduction (\hat{q}_{c} ;) electrons w ith B loch m om entum k and sp in = 1=2, interacting antiferrom agnetically w ith the localized f electrons in a lattice w ith N $_{\rm S}$ sites:

with J < 0, and the spin operators at site i are given by $\hat{s}_i = \hat{c}_{i,}^y$ \hat{c}_i , and $\hat{S}_i = \hat{f}_{i,}^y$ \hat{f}_i , (are Paulimatrices). There is exactly one f electron at each site. In order to describe the spin singlet formation between c and f electrons at every site in the HFL phase, we recast the local spin exchange interaction as \hat{s}_i \hat{S}_i =

 $\hat{\ }_{i,"} + \ _{i,\#} \qquad \hat{\ } \hat{\ }_{c;i} \qquad \hat{\ } \hat{\ }_{f;i} \qquad \hat{\ } \hat{\ }_{c;i} \hat{\ } \hat{\ }_{f;i} \text{, where } \hat{\ }_{c(f);i} \text{ is the number operator for c (f) electron at site i and } \\ \hat{\ }_{i} \ = \ \frac{1}{2} \quad \hat{\ }_{i;}^{V} \quad \hat{\ } \hat{\ }_{i;} \ + \ h \text{ : . We decouple the $^{\circ}$ operators by introducing an auxiliary eld, , so the elective mean eld theory becomes 4:}$

In the HFL phase ($\upliese 0$) quasi-particles form , with momentum k, having c and f components. We shall assume that only the lowest band E (k) of heavy quasi-particles is occupied. In the \normal" phase (= 0) quasi-particles are just c electrons. Single particles are described by

two-component wave-functions (r) = (u(r);v(r)) related to the c and f components of the electronic states, respectively, and obeying the normalization condition $\dot{y}(r)\dot{f} + \dot{y}(r)\dot{f} = 1$. In homogeneous heavy fermion metals we have $(u(r);v(r)) = (u_k;v_k)e^{ik}$, with

$$u_k^2 = \frac{(2 \text{ J})^2}{(2 \text{ J})^2 + (E \text{ (k)})^2};$$
 (3)

$$v_k^2 = \frac{(E (k))^2}{(2 J)^2 + (E (k))^2};$$
 (4)

and the energy of this state is

E (k) =
$$\frac{1}{2}$$
 f + (k) $\frac{q}{(f (k))^2 + (4 J)^2}$: (5)

In a norm alhom ogeneous metal $u_k=1$ for a celectron and $v_k=1$ for a local f electron. The self-consistent equation for is: = $(4N_s)^{1}$ $_{i_1}$, $hc_{i_2}^{v_1}$, f_{i_3} , + h ci: In mean eld theory, the local chem ical potential $_f$ for the f electrons must be chosen so as to implement single occupancy on average, $hf_{f,i}i=1$, at every site i. Therefore, in a inhom ogeneous system $_f$ may be required to vary from site to site. In the HFL phase $_f$ 0 and both c and f electrons contribute to the FS volume. Therefore, the volume of the FS must either include n_c electrons in the norm alm etalor $1+n_c$ electrons in the heavy ferm ion metal.

We now consider a system where both HFL and normal phases exist simultaneously and are separated by a thin interface. We take half of the metal (x < 0) to be in the HFL phase while the other x > 0 half is in the normal state (=0). The interface is the yz plane. We shall denote by p the Bloch wave-vector in the heavy metal and by k the wave-vector in the normal metal.

III. IN TERFACE PROPERTIES

${\tt A}$. ${\tt A}\,{\tt b}\,{\tt sence}$ of a proxim ity e ect

If we consider that J = 0 on the normal x > 0 half of the metal, then the amplitude for singlet formation, $h\hat{c}_{i:}^{y}$, $f_{i:}$, i, drops abruptly from its nite value in the heavy ferm ion (x < 0) m etal, to zero in the normal m etal¹². The local singlet correlation vanishes abruptly as one goes from the heavy to the normalmetalbecause of the localized nature of the f electrons. In this sense, we m ay say that there is no proxim ity e ect for singlet formation. In a normal-superconductor interface there is a proxim ity e ect for the pairing, hci; ci; i, because the electrons establish the Cooper pairing in the superconductor and they both propagate into the normal side transporting the correlation with them. This does not happen in the case discussed here since the f electrons are localized. The coupling J = 0 on the normal side e ectively removes the normal metal flocal moments

from the problem, so they cannot establish singlet correlations with conduction electrons. Nevertheless, there is a singlet correlation between a conduction electron on the normal side (close to the interface) and a f m om ent on the heavy metal side. The same happens if, instead of taking J = 0, a su ciently strong magnetic eld is applied to the x > 0 portion of the m etal which polarizes the f m om ents, thereby preventing the form ation of spin singlets. A Itematively, we may consider a temperature gradient, such that the left side of the sample is below the K ondo tem perature, $T_{\rm K}$, and the right hand side is above T_K . Then $h \hat{c}^V_{i;}$ $f_{i;}$ i decreases continuously to zero as the tem perature crosses $T_{\mbox{\scriptsize K}}$. The coherence factors of the quasi-particles u and v vary continuously in space but the FS volume of carriers changes abruptly in a very thin region where! 0. The absence of a proximity e ect is rather in portant in the case of inhom ogeneous alloys because it shows that the heavy-ferm ion component of the system cannot penetrate the light component. The situation here is sim ilar to the one in optics where light com ing to an interface between two materials with very di erent index of refraction is completely re ected at the interface.

B. Form ation of a dipole barrier

The spin singlet formation between localized f and conduction electrons lowers the electron local site energy of the c electron. This causes the chemical potential of a heavy ferm ion system to be lower than that of a norm alm etalw ith the same conduction electron concentration n_c. It implies that some conduction electrons initially ow through the interface, leaving a positive excess charge in the normal metal side and a negative excess charge on the heavy ferm ion side. Therefore, a dipole barrier form s close to the interface. The electrostatic potential created by the barrier (sim ilar to that of a capacitor) increases the local site energy of the celectrons on the heavy ferm ion subsystem by an amount c with respect to the local c site energies in the normal subsystem (the situation here resembles the contact potential of a dipole layer in p-n sem iconductor junctions). The chemical potential is then constant throughout the sam ple but the c site energies increase by the amount c across the barrier from the normal to the heavy ferm ion side. Because these are metallic systems, the dipole barrier should be e ciently screened by the conduction electrons over a length of the order of few atom ic spacings12.

The local site site energy of the c electrons varies in space close to the interface, $_{c}(x) = eV(x)$ where V(x) is the electrostatic potential and e is the electron charge. It is assumed that V(x) ! 0 as x ! 1 deep inside the normal metal (see Figure 2). The Poisson equation for the local site energy reads

$$\frac{d^{2}_{c}(x)}{dx^{2}} = \frac{e^{2}}{"_{0}} [n_{c}(x) \quad n_{c}];$$
 (6)

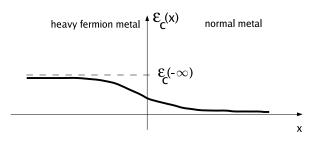


FIG. 2: Spatial variation of the c site energies due to the form ation of a dipole barrier at the interface.

where " $_0$ is the vacuum electrical perm it ivity, $n_{\rm c}\left(x\right)$ denotes the space dependent c electron concentration and the value of $n_{\rm c}=n_{\rm c}\left(\ 1\ \right)$ is determ ined by charge neutrality away from the interface. An analytical description of the dipole barrier can be made using a Thom as Ferm i approximation where the Fermimomenta are assumed to vary in space. On the heavy fermion side (x < 0), using a parabolic dispersion, one can write:

$$= \frac{1}{2} \frac{-^{2}p_{F}^{2}(x)}{2m} + _{c}(x) + _{f}$$

$$= \frac{1}{2} \frac{-^{2}k_{F}^{2}(x)}{2m} + _{c}(x) + _{f}$$

$$= \frac{1}{2} \frac{-^{2}k_{F}^{2}(x)}{2m} + _{c}(x) + _{f}$$
3
$$= \frac{1}{2} \frac{-^{2}k_{F}^{2}(x)}{2m} + _{c}(x) + _{f}$$
3

$$n_c(x) = \frac{2}{(2)^3} \int_0^{Z_{p_F}(x)} d^3p \, u_p^2(x);$$
 (8)

while on the normalmetal side we write:

$$= \frac{\sim^2 k_F^2 (x)}{2m} + _{c}(x); \qquad (9)$$

$$n_c(x) = \frac{2}{(2)^3} \frac{4}{3} k_F^3(x)$$
: (10)

E lim inating k_F (x) from (9)- (10) and solving for n_c (x), we can then insert the result in (6) obtaining:

$$\frac{d^{2}_{c}(x)}{dx^{2}} = \frac{e^{2}}{"_{0}} \frac{2m}{\sim^{2}} \frac{\left(\frac{2}{3}(x)\right)^{\frac{3}{2}}}{3^{2}} n_{c}; (11)$$

for x > 0.But

$$n_c = \frac{2m}{2} = \frac{\frac{3}{2}}{\frac{3}{2}} = \frac{\frac{3}{2}}{\frac{3}{2}}$$
;

therefore,

$$\frac{d^{2}_{c}(x)}{dx^{2}} = \frac{e^{2}}{\P_{0}} \frac{1}{3^{2}} \frac{2m}{2} \frac{e^{2}}{2^{2}} \frac{1}{2^{2}} \frac{h}{(c(x))^{\frac{3}{2}}} \frac{1}{3^{\frac{3}{2}}} \frac{1}{2^{\frac{3}{2}}} \frac{1}{2^{\frac{3}{2}}} \frac{1}{2^{2}} c(x)$$
(12)

im plying that $_{c}(x) = _{c}(0)e^{x-n}$ with the screening length inside the normal metal given by:

$$_{\rm n}^2 = \frac{{\rm e}^2 {\rm m} \, {\rm k}_{\rm F}}{{\rm m}_{\rm o} \sim^{2-2}} :$$
 (13)

Considering the heavy ferm ion side (x < 0), we may directly write the variation in c-electron density already linearized in the energy shift of the site energies:

$$n_c(x)$$
 $n_c = N_{F(h)}[c(x) c(1)];$ (14)

where $N_{F(h)}$ denotes the Ferm i level density of states of the heavy ferm ion system (which can be taken at x=1) and is given by

$$N_{F(h)} = \frac{2}{(2)^3} Z^3 d^3p \quad (E(p)) = \frac{m p_F}{2 \sim^2 u^2 (p_F)}$$
:
(15)

Then the linearized version of the Poisson equation (6) becomes:

$$\frac{d^{2}_{c}(x)}{dx^{2}} = \frac{e^{2}}{\mathbf{v}_{0}} \frac{m p_{F}}{2 \sim^{2} u^{2}(p_{F})} [c(x) c(1)]; \quad (16)$$

which gives

$$_{c}(x) = _{c}(1) + [_{c}(0) _{c}(1)]e^{x = h};$$
 (17)

with the screening length on the heavy metal side given by

$$_{h}^{2} = \frac{e^{2}m p_{F}}{m_{0} \sim^{2} 2u^{2} (p_{F})}$$
: (18)

The value of p_F can be simply obtained from the condition of charge neutrality far from the interface,

$$\frac{2}{(2)^3} \quad d^3p = 1 + n_c : \tag{19}$$

C. Transm ission through the interface

The two-component wave-function (r) varies across the interface in such a way that it describes a heavy quasiparticle for x < 0 and a c or localized f electron for x > 0. The f electrons are localized and therefore carry no charge current. It is only the celectron that transports charge (across the interface). This can also be readily seen from them icroscopic conservation of the probability, $(0,1)^2 = (1,1$

The m atching conditions to be imposed on the wave-function are the continuity of u(r) and the current conservation, which is only related to u(r). In a model with parabolic electronic dispersion, $(k)/k^2$, this would imply the continuity of the gradient of u(r). The function

v(r) itself obeys no m atching condition: v(r)=1 (or 0) for a f (or c) electron on the norm al (= 0) side and, in the HFL side, where 60, v(r) is determined by the diagonalization of the H am iltonian (2) and the m atching condition for v(r).

In a model where changes abruptly from a nite value to zero at the interface, the local chem ical potential $_{\rm f}$ and the celectron site energy $_{\rm c}$ vary in space in a small region close to the interface. In the following we neglect this spatial variation and assume that $_{\rm c}>0$ is constant for x < 0 and $_{\rm c}=0$ for x > 0, and that $_{\rm f}$ also changes abruptly from its constant bulk value in the heavy ferm ion x < 0 to $_{\rm f}=$ for x > 0. In order to calculate the conductance through the interface, we consider a model parabolic dispersion for the celectrons. The B loch wave-vector has both parallel (k $_{\rm jj}$) and perpendicular (k $_{\rm x}$) components to the interface. Introducing the position vector r = (y;z), the matching conditions for the wave-function describing an incident quasi-particle from the left in ply p $_{\rm ji}=k_{\rm ji}$:

$$_{L}$$
 $(x < 0) = e^{i p_{jj} r}$ u $e^{ip_{x} x} + r_{k,p}$ u $e^{ip_{x} x}$;

$$_{L}(x > 0) = t_{k,p} \frac{1}{0} e^{ik_{x}x} e^{i p_{jj} r};$$
 (20)

with the transmission and rejection amplitudes given by:

$$t_{k,p} = u \frac{2p_x}{p_x + k_x}; \qquad r_{k,p} = \frac{p_x - k_x}{p_x + k_x};$$
 (21)

respectively. The momenta satisfy the energy conservation condition E $p_{jj};p_x=k_{jj}=p_{jj};k_x$. Because the heavy ferm ion metal has the larger FS only incident electrons from the left making an angle < arcsin ($k_F=\!\!p_F$) with the x axis are transmitted (see Fig. 1). A wavefunction describing an incident conduction electron from the right is given by:

$$_{R} (x < 0) = t_{p; k} e^{i k_{jj} r} u e^{i p_{x} x};$$
 (22)

$$_{R} (x > 0) = e^{i k_{jj} r} \frac{1}{0} e^{i k_{x} x} + r_{p; k} \frac{1}{0} e^{i k_{x} x}$$

with the transmission and rejection amplitudes given by:

$$t_{p;k} = \frac{1}{u} \frac{2k_x}{p_x + k_x}; \quad r_{p;k} = \frac{k_x - p_x}{p_x + k_x}; \quad (23)$$

respectively.

D. Conductance through the interface

The transm ission and re ection am plitudes are determined by the m ism atch of the Ferm im om enta of the two subsystems. Applying a voltage V across the interface, the charge current owing from right to left is 13:

$$I = 2e^{2}VS \frac{d^{3}k}{(2)^{3}} (k) \frac{dE}{e^{2}p_{x}} t_{p; k} f (24)$$

where S denotes the area of the interface. It can be shown from (5) that the heavy particle velocity $@E(p) = @p_x = u^2@(p) = @p_x . Equation (24)$ can be written as:

$$I = 2e^{2}VS \int_{0}^{Z} d \sin d \frac{Z_{1}}{u} \frac{k^{2} dk}{(2)^{3}}$$

$$(\sim v_{F} (k k_{F})) \frac{u^{2} \sim p_{x}}{m} \frac{2k_{x}}{u (k_{x} + p_{x})}^{2}$$
 (25)

The integration is perform ed in the halfsphere $\ < \ = 2$ of incident m om enta from the norm alm etal. On the Ferm i Surface we write $k_x = k_F$ cos and $p_k = p_F$ cos . The m om enta on both sides of the interface are related by $p_F^2 = p_{jj}^2 + p_x^2$ and $k_F^2 = k_{jj}^2 + k_x^2$ with $p_{jj} = k_{jj} = k_F$ sin . Therefore, we can rewrite (25) as

The conductance of a clean heavy ferm ion metal is given by

$$G_{0h} = S \frac{e^2}{h} \frac{p_F^2}{2}$$
: (27)

The conductance of the interface, $G_i (= I=V)$, obtained from equation (26) after changing the variable of integration to $x = \sin is$:

$$\frac{G_{i}}{G_{0h}} = 8^{3} \int_{0}^{Z_{1}} dx \frac{p_{1} - x^{2}}{p_{1} - x^{2}} \frac{p_{1} - 2x^{2}}{p_{1} - 2x^{2}}; \quad (28)$$

where $^3=(k_F\!=\!\!p_F\!)^3=n_c\!=\!(1+n_c)$. Figure 3 shows a plot of the interface conductance versus n_c . One can clearly see that the larger the value of n_c the larger is the e ect and even for dense systems with $n_c=1$ electron per unit cell (half-lling) the value of the interface conductance is of the order of 60 % of that of a clean heavy ferm ion m etal.

IV. EXPERIMENTAL REALIZATION

In the geometry suggested in Fig. 1 with the heavy-ferm ion, the normal ferm ion, and the interface in series, one would measure the total conductance of the junction, that is, $G^{-1} = G_h^{-1} + G_n^{-1} + G_i^{-1}$, where G_n is the conductance of the normal Ferm i liquid. Hence, in order to measure the interface conductance one would have to measure the heavy and normal conductance separately, before measuring the conductance of the interface. The bulk conductance of the heavy ferm ion can be expressed as

$$G_h = S \frac{e^2}{h} \frac{p_F^2}{2} \frac{c}{L};$$
 (29)

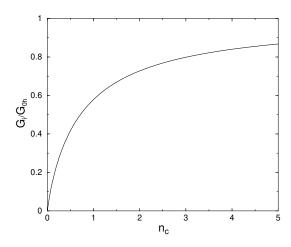


FIG. 3: Interface conductance (normalized to that of a clean heavy ferm ion metal) plotted versus conduction electron density.

where $'_c$ is 4=3 of the electron's transport mean-free path and L is the size of the system (in the clean limit, $'_c > L$, we set L= $'_c$ = 1 in (29)). Electron scattering by impurities and phonons are included in the bulk conductances. The point we wish to emphasize is that the interface itself causes a contribution to the total resistance.

The interface can be created avoiding large lattice m ism atches between the two sides, so as to m in im ize structural scattering. Here we suggest a few possibilities: (1) in the scenario of Figure 4a, a large magnetic eld can be applied to one side of the sample and the longitudinal resistivity can be measured with and without the eld; (2) a sharp tem perature gradient can be applied to a sample of a heavy ferm ion material so that half of the system is above the K ondo temperature and half is below the K ondo tem perature. Heavy ferm ion materials have resistivity (T) / logT above the K ondo tem perature T_K and (T) decreases rapidly as tem perature is reduced below $\,T_{K}\,$. If a constant tem perature dierence is in posed across the sample with them al conductivity K , a heat current j_Q = K dT = dx ows. From the W iedem ann-Franz law we expect $dT = dx / T^{-1}$ (T). If a material with a sharp resistivity peak near the Kondo tem perature is chosen, then the tem perature gradient is high in the region where T T_K , producing a thin interface. In this case, the material must be chosen so as to m in im ize e ects associated with them oelectric power; (3) in the scenario of Figure 4b, for systems where the m agnetic behavior can be tuned by changing the chem ical concentration (chem ical pressure), a sam ple could be grown with a large gradient concentration so that half of the system is in the magnetically ordered phase and half in the HFL phase; (4) alternatively, two dierent mechanical pressures can be applied on two regions of the sam ple, so that the two regions are on opposite sides of a QCP, as the points A and B in Figure 4b. If the QCP occurs at vanishing K ondo tem perature, $T_{K}^{\;(1)}$, the sharp

FS volumem is match at the interface causes the elects predicted above.

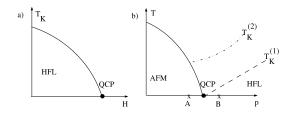


FIG. 4: a) The Kondo temperature decreases under external magnetic eld and vanishes at a quantum critical point (QCP); b) phase diagram showing the QCP between an antiferrom agnetic metal (AFM) and HFL phases, obtained by varying pressure.

In systems where the Kondo temperature is nite at the QCP ($T_{\rm K}^{~(2)}$ in Fig. 4(b)), we believe the interface scattering between the AFM and the HFL phases to be negligible small (and would anyway disappear as A and B approach the QCP). This can be seen as follows. The AFM, in this case, is a spin-density-wave (SDW) in a system where the local magnetic moments have been K ondo screened by the conduction electrons. Some regions of the Ferm i surface are gapped. Now suppose that the electrons ow from the SDW to the paramagnetic phase. Only the electrons in the ungapped regions of the Ferm i surface produce a current. An ungapped electron ows from the SDW into the param agnetic phase without changing its B loch k state. If an interface scattering exists at all, it should be very small, unlike the one predicted above for the Kondo screening scenario, which is caused by an appreciable momentum mismatch around the whole Ferm i surface. Therefore, we believe that an experimental setup like the one we propose can distinguish the two scenarios ($T_{\rm K}^{(1)}$ and $T_{\rm K}^{(2)}$ in Fig. 4(b)) for the QCP in heavy ferm ion systems, because in the SDW scenario the interface scattering e ect should be almost non-existent.

In sum mary, we have studied the problem of the transport through an interface between a heavy electron m etal and an ordinary metal. We have argued that the heavy ferm ion state does not induce a proximity e ect on the ordinary metal and that the hybridization gap changes abruptly across the interface. Because of the change of the f electron energy across the interface an atom ically thin dipole barrier is form ed, a situation quite similar to the dipole layers in semiconducting p-n junctions. We have also shown that the interface produces a contribution to the electrical conductance that depends essentially on the number of electrons in the system and that for dense systems the value of the conductance is substantial and can be easily m easured experim entally. We have also proposed ways to create such interfaces. We hope this work will stimulate experimentalists to realize them experim entally. Finally, we would like to stress that our results not only have implications for the problem of the nature of the heavy electron ground state, but also can be used to understand quantum criticality and the e ects of inhom ogeneities close to quantum critical points.

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